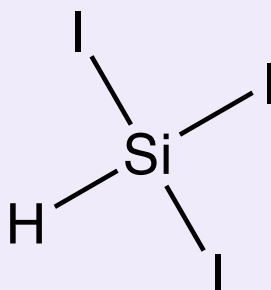
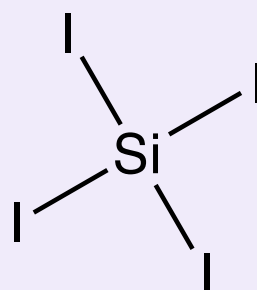


SID3520.1

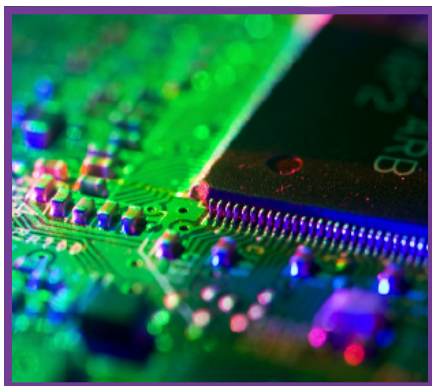


SIT8378.56



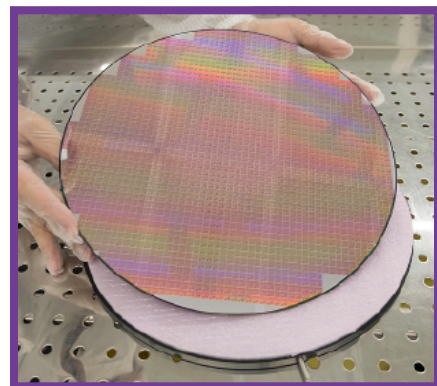
SIT7123.0

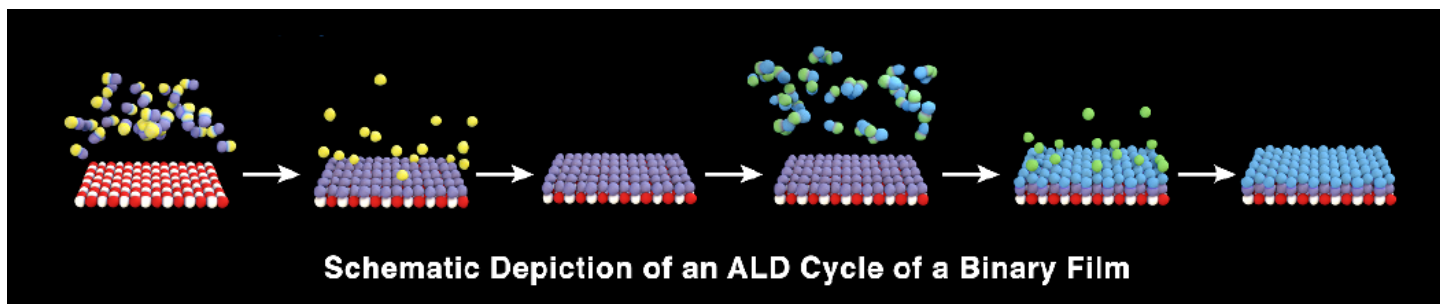
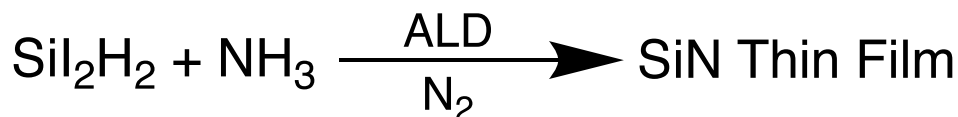
Properties	Diiodosilane	Triiodosilane	Tetraiodosilane
Product Code	SID3520.1	SIT8378.56	SIT7123.0
Chemical Formula	SiH_2I_2	SiHI_3	SiI_4
CAS Number	13760-02-6	13465-72-0	13465-84-4
Vapor Pressure	55 °C at 25 Torr	95 °C at 12 Torr	125 °C at 30 Torr
Phase	Liquid	Liquid	Solid
Molecular Weight (g/mol)	283.91	409.81	535.7
Boiling Point (°C)	149-150	220	287-8
Melting Point (°C)	-1	8	120-1



Iodosilane Applications

- Semiconductor Fabrication
 - SiN thin films
 - a-Si thin films
- Pharmaceutical Synthesis
 - Reductive iodination
 - Synthesis of acyl iodides

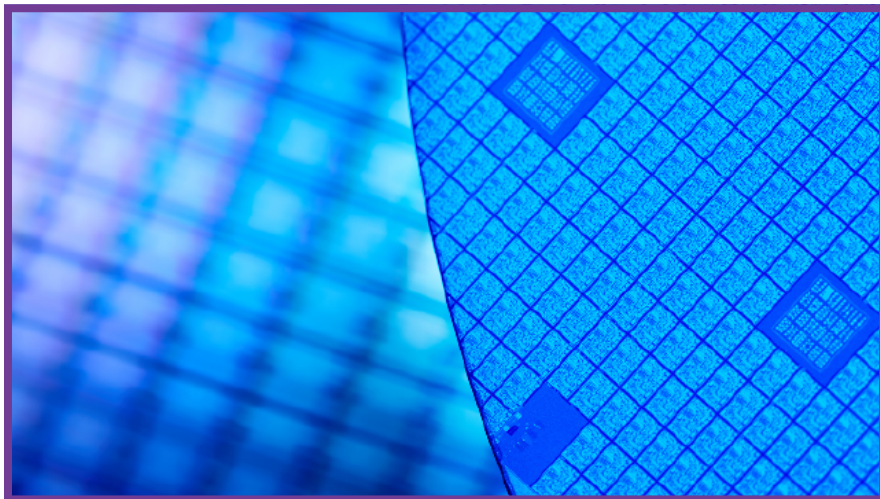




Iodosilane precursors are used to deposit silicon and silicon nitride (SiN) thin films with high conformality and low thermal budget. High purity grades of diiodosilane in excess of 99.9% are commercially available from Gelest.

Benefits of Iodosilanes

- Low Thermal Budget
- Stable Vapor Phase
- Highly Conformal Thin Films



Additional Information:

1. Kaloyeros, A. *et al ECS Journal of Solid State Science and Technology* **2017**, 6(10), P691-P9714
2. Arkles, B. *et al Solid State Technologies*, January/February 2018, pg 22-24
3. Tamizhmani, G. *et al Chem. Mater.* **1990**, 2, 473-476